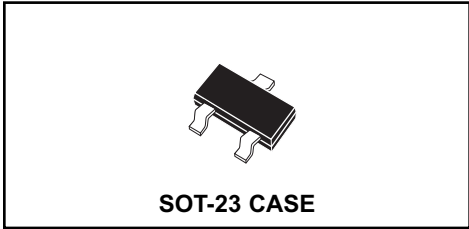




BCV72
SURFACE MOUNT
SILICON NPN TRANSISTOR



CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BCV72 is a Silicon NPN Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose applications.

MARKING CODE: K8

MAXIMUM RATINGS: (T_A=25°C)

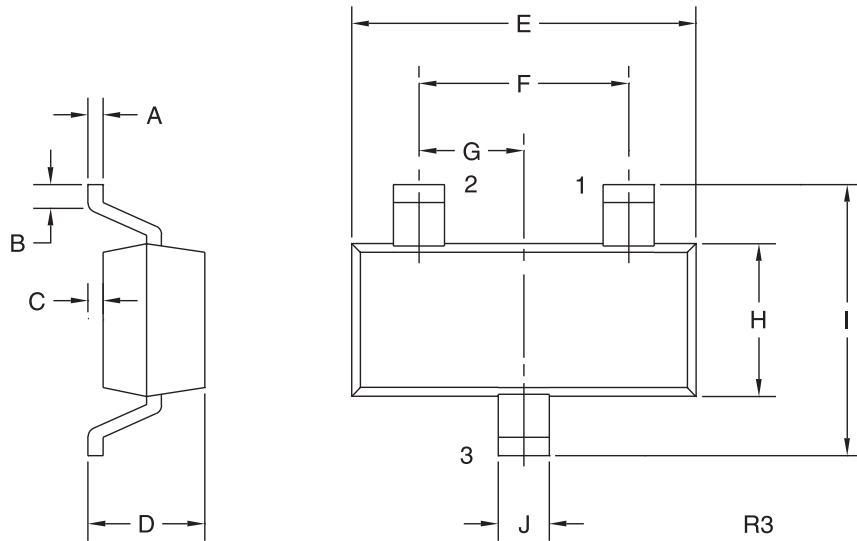
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

SYMBOL		UNITS
V _{CBO}	80	V
V _{CEO}	60	V
V _{EBO}	5.0	V
I _C	100	mA
I _{CM}	200	mA
P _D	350	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =20V			100	nA
I _{CBO}	V _{CB} =20V (T _A =100°C)			10	μA
BV _{CEO}	I _C =2.0mA	60			V
BV _{CBO}	I _C =10μA	80			V
BV _{EBO}	I _C =10μA	5.0			V
V _{CE(SAT)}	I _C =10mA, I _B =0.5mA			250	mV
V _{BE(ON)}	V _{CE} =5.0V, I _C =2.0mA	550		700	mV
h _{FE}	V _{CE} =5.0V, I _C =2.0mA	200		450	
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		2.5		pF
f _T	V _{CE} =5.0V, I _C =10mA, f=35MHz		300		MHz
NF	V _{CE} =5.0V, I _C =200μA, R _S =2.0kΩ f=1.0kHz, B=200Hz			10	dB

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: K8

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)